PTO/SB/084(10-01)
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INFORMATION DISCLOSURE	Application Number	10/053,003	RECEIVER		
STATEMENT BY APPLICANT	Filing Date	January 17, 2002			
\$\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	First Named Inventor	Forbes, Leonard	OCT 2 4 2003		
0CT 2 0 2003 (#)	Group Art Unit	1765	TO 4700		
A SEPTIMENT OF THE PROPERTY OF	Examiner Name	Kunemund, Robert	10 1700		
Sheet 1 of 2	Attorney Docket No: 1303.042US1				

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